**Features:**

- n** Isolated mounting base 3000V~
- n** Pressure contact technology with Increased power cycling capability
- n** Space and weight saving

Typical Applications

- n** Various rectifiers
- n** DC supply for PWM inverter

V_{RRM}	Type & Outline
800V	MDx1000-08-411F3
1000V	MDx1000-10-411F3
1200V	MDx1000-12-411F3
1400V	MDx1000-14-411F3
1600V	MDx1000-16-411F3
1800V	MDx1000-18-411F3
1800V	MD1000-18-411F3G

MDx stands for any type of **MDC**, **MDA**, **MDK**

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_j(^{\circ}\text{C})$	VALUE			UNIT
				Min	Type	Max	
$I_{F(AV)}$	Mean forward current	180° half sine wave 50Hz Single side cooled, $T_c=60^{\circ}\text{C}$	150			1000	A
$I_{F(RMS)}$	RMS forward current					1570	A
I_{RRM}	Repetitive peak current	at V_{RRM}	150			40	mA
I_{FSM}	Surge forward current	$V_R=60\%V_{RRM}$, $t=10\text{ms}$ half sine	150			24	kA
I^2t	I^2t for fusing coordination					2880	$10^3\text{A}^2\text{s}$
V_{FO}	Threshold voltage		150			0.75	V
r_F	Forward slope resistance					0.25	$\text{m}\Omega$
V_{FM}	Peak forward voltage	$I_{FM}=3000\text{A}$	25			1.58	V
$R_{th(j-c)}$	Thermal resistance Junction to case	Single side cooled per chip				0.065	$^{\circ}\text{C/W}$
$R_{th(c-h)}$	Thermal resistance case to heatsink	Single side cooled per chip				0.018	$^{\circ}\text{C/W}$
V_{iso}	Isolation voltage	50Hz, R.M.S, $t=1\text{min}$, $I_{iso}=1\text{mA}(\text{MAX})$		3000			V
F_m	Terminal connection torque(M12)			12		16	N·m
	Mounting torque(M8)			10		12	N·m
T_{vj}	Junction temperature			-40		150	$^{\circ}\text{C}$
T_{stg}	Stored temperature			-40		125	$^{\circ}\text{C}$
W_t	Weight				3230		g
Outline	411F3						

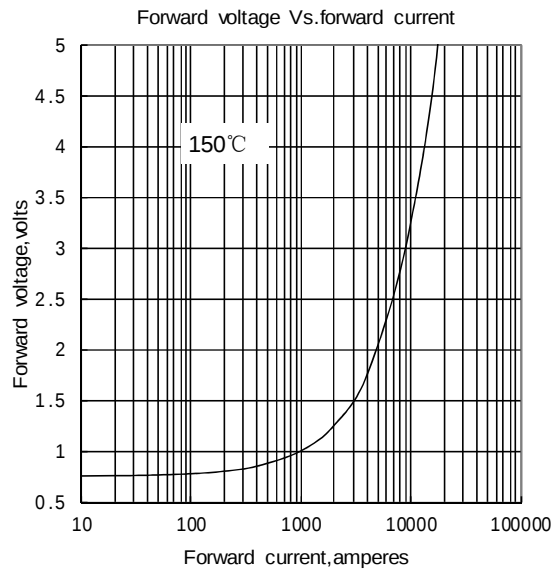


Fig.1

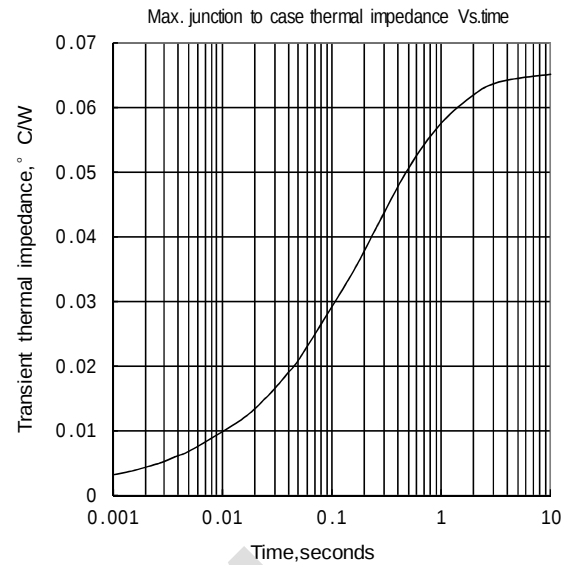


Fig.2

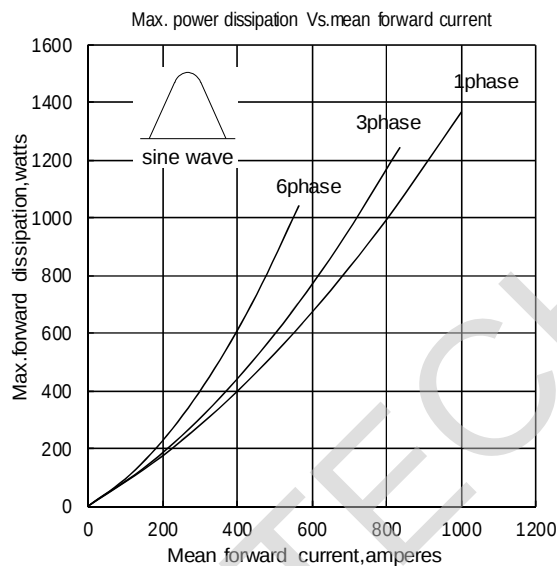


Fig.3

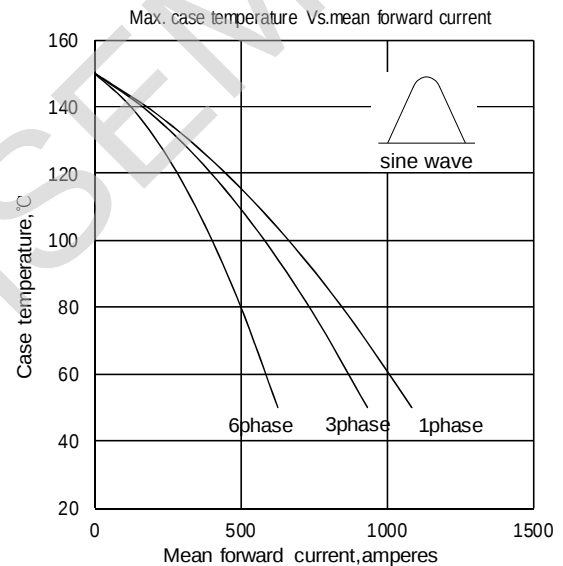


Fig.4

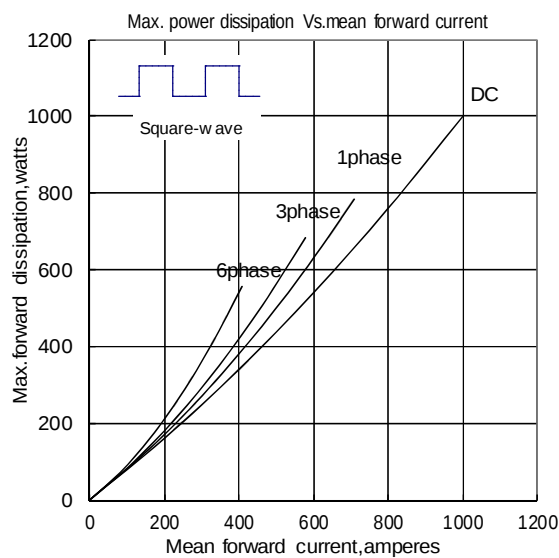


Fig.5

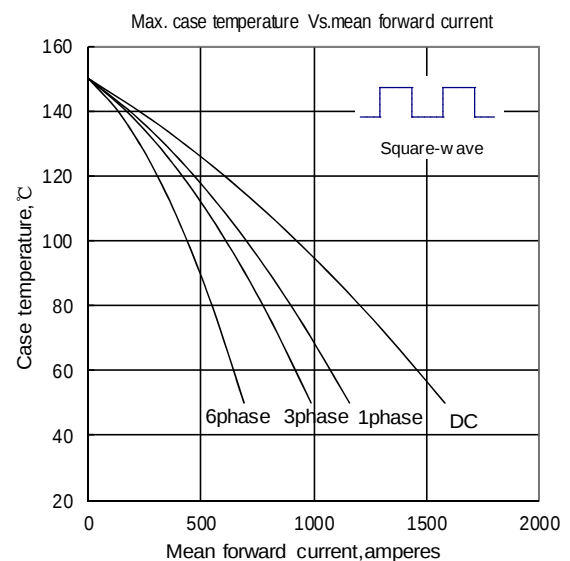


Fig.6

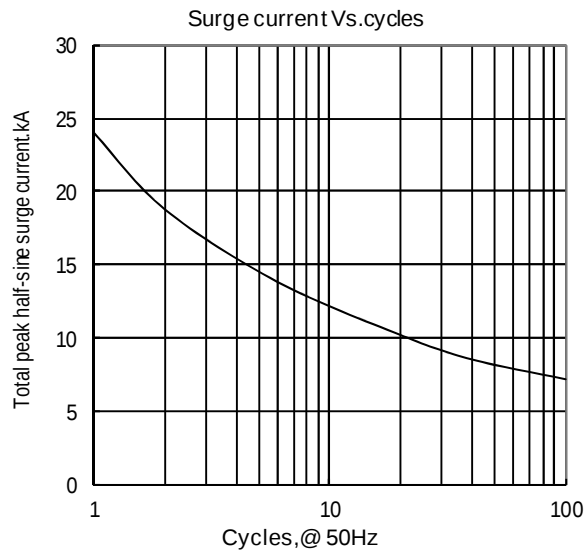


Fig.7

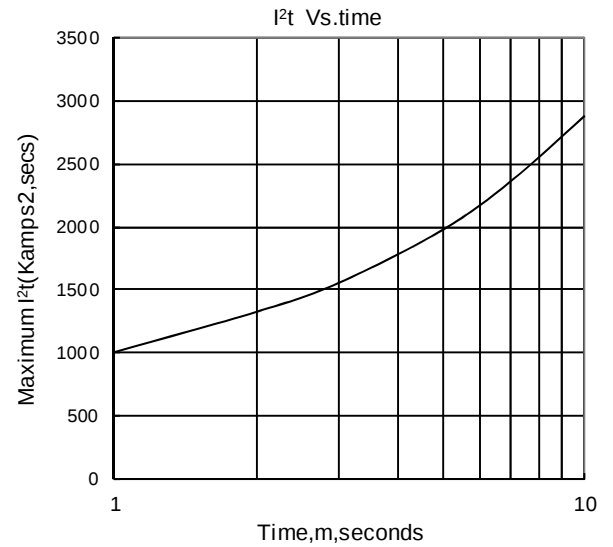
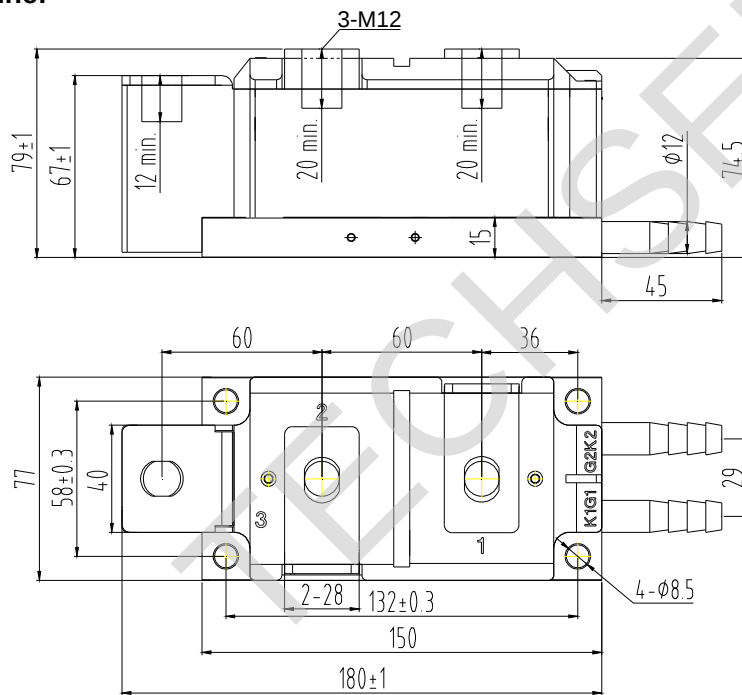


Fig.8

Outline:Unmarked dimensional tolerance: $\pm 0.5\text{mm}$ 